



CY62137V MoBL®

2-Mbit (128K x 16) Static RAM

Features

- **Temperature Ranges**
 - Commercial: 0°C to 70°C
 - Industrial: -40°C to 85°C
 - Automotive: -40°C to 125°C
- **High Speed: 55 ns and 70 ns**
- **Wide voltage range: 2.7V–3.6V**
- **Ultra-low active, standby power**
- **Easy memory expansion with \overline{CE} and \overline{OE} features**
- **TTL-compatible inputs and outputs**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Package Available in a standard 44-pin TSOP Type II (forward pinout) package**

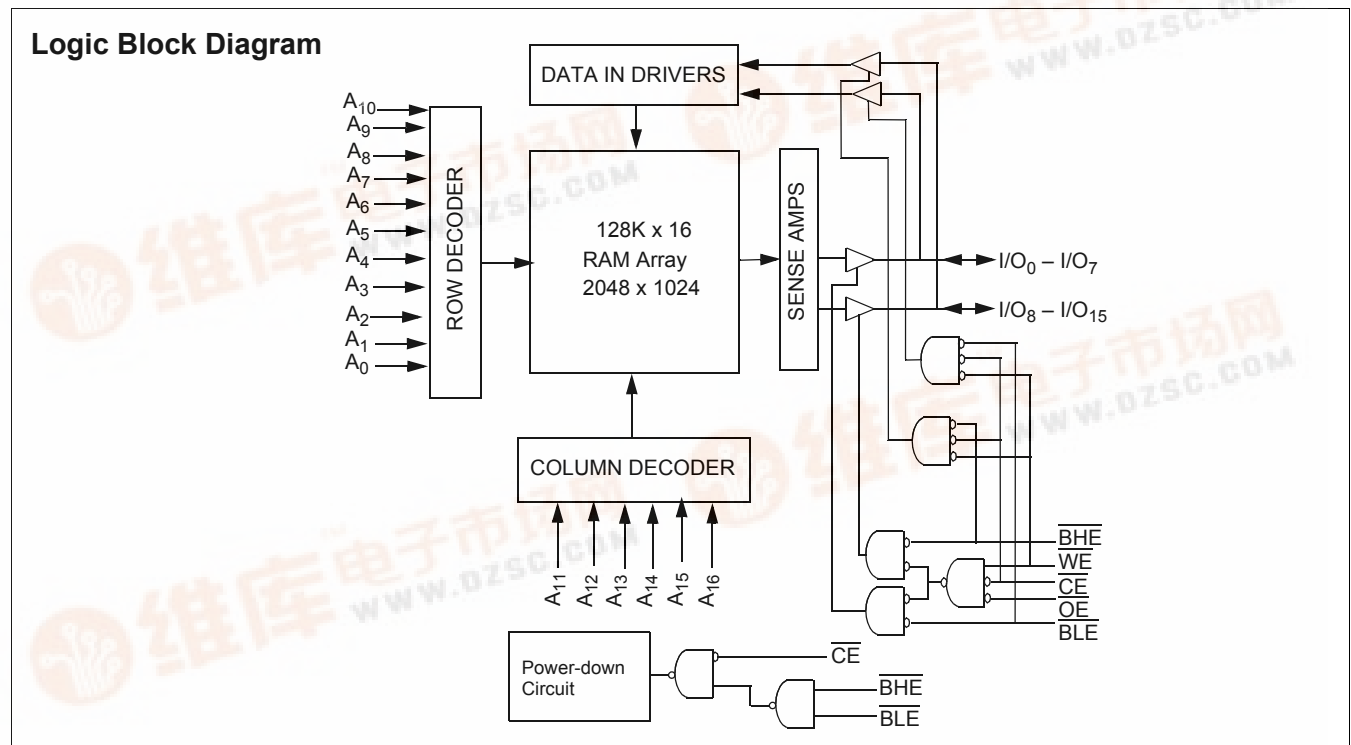
Functional Description^[1]

The CY62137V is a high-performance CMOS static RAM organized as 128K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life® (MoBL®) in portable applications such as cellular telephones. The device

also has an automatic power-down feature that reduces power consumption by 99% when addresses are not toggling. The device can also be put into standby mode when deselected (\overline{CE} HIGH) or when \overline{CE} is LOW and both \overline{BLE} and \overline{BHE} are HIGH. The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected (\overline{CE} HIGH), outputs are disabled (\overline{OE} HIGH), \overline{BHE} and \overline{BLE} are disabled (\overline{BHE} , \overline{BLE} HIGH), or during a write operation (\overline{CE} LOW, and \overline{WE} LOW).

Writing to the device is accomplished by taking Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. If Byte Low Enable (\overline{BLE}) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{16}). If Byte High Enable (\overline{BHE}) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) LOW while forcing the Write Enable (\overline{WE}) HIGH. If Byte Low Enable (\overline{BLE}) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7 . If Byte High Enable (\overline{BHE}) is LOW, then data from memory will appear on I/O_8 to I/O_{15} . See the truth table at the back of this data sheet for a complete description of read and write modes.



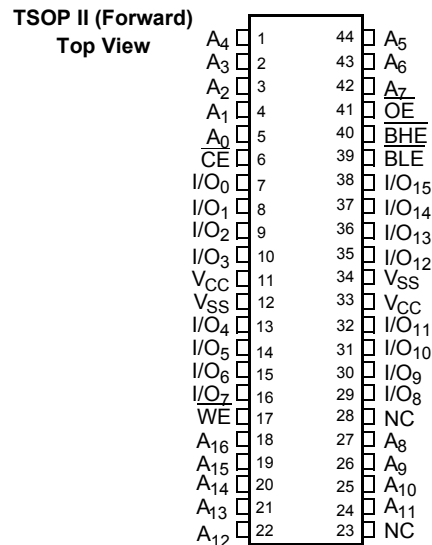
Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.



Product Portfolio

Product		V _{CC} Range (V)			Speed (ns)	Power Dissipation			
						Operating, I _{CC} (mA)		Standby, I _{SB2} (μA)	
		Min.	Typ. ^[3]	Max.		Typ. ^[3]	Max.	Typ. ^[3]	Max.
CY62137VLL	Industrial	2.7	3.0	3.6	55	7	20	1	15
CY62137VSL					55	7	20	1	5
CY62137VLL					70	7	15	1	15
CY62137VSL					70	7	15	1	5
CY62137VLL	Automotive				70	7	15	1	20

Pin Configurations

Pin Definitions

Pin Number	Type	Description
1-5, 18-22, 24-27, 42-45	Input	A ₀ -A ₁₆ . Address Inputs
7-10, 13-16, 29-32, 35-38	Input/Output	I/O ₀ -I/O ₁₅ . Data lines. Used as input or output lines depending on operation
23	No Connect	NC. This pin is not connected to the die
17	Input/Control	WE. When selected LOW, a WRITE is conducted. When selected HIGH, a READ is conducted
6	Input/Control	CE. When LOW, selects the chip. When HIGH, deselects the chip
39, 40	Input/Control	BHE, BLE. BHE = LOW selects higher order byte WRITES or READs on the SRAM. BLE = LOW selects lower order byte WRITES or READs on the SRAM
41	Input/Control	OE. Output Enable. Controls the direction of the I/O pins. When LOW, the I/O pins behave as outputs. When deasserted HIGH, I/O pins are three-stated, and act as input data pins
12, 34	Ground	V _{SS} . Ground for the device
11, 33	Power Supply	V _{CC} . Power supply for the device

Notes:

- NC pins are not connected on the die.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(TYP)}, T_A = 25°C.



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

- Storage Temperature -65°C to +150°C
- Ambient Temperature with Power Applied -55°C to +125°C
- Supply Voltage to Ground Potential -0.5V to +4.6V
- DC Voltage Applied to Outputs in High-Z State^[4] -0.5V to V_{CC} + 0.5V
- DC Input Voltage^[4] -0.5V to V_{CC} + 0.5V

- Output Current into Outputs (LOW) 20 mA
- Static Discharge Voltage > 2001V (per MIL-STD-883, Method 3015)
- Latch-up Current > 200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Industrial	-40°C to +85°C	2.7V to 3.6V
Automotive	-40°C to +125°C	2.7V to 3.6V

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	CY62137V-55			CY62137V-70			Unit
			Min.	Typ. ^[3]	Max.	Min.	Typ. ^[3]	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -1.0 mA, V _{CC} = 2.7V	2.4			2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 2.1 mA, V _{CC} = 2.7V			0.4			0.4	V
V _{IH}	Input HIGH Voltage		2.2		V _{CC} + 0.5V	2.2		V _{CC} + 0.5V	V
V _{IL}	Input LOW Voltage		-0.5		0.8	-0.5		0.8	V
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}	-1		+1	-1		+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled	-1		+1	-1		+1	μA
I _{CC}	V _{CC} Operating Supply Current	I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{RC} , CMOS Levels		7	20		7	15	mA
		I _{OUT} = 0 mA, f = 1 MHz, CMOS Levels		1	2		1	2	mA
I _{SB1}	Automatic CE Power-down Current— CMOS Inputs	CE ≥ V _{CC} - 0.3V, V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V, f = f _{MAX}			100			100	μA
I _{SB2}	Automatic CE Power-down Current— CMOS Inputs	CE ≥ V _{CC} - 0.3V, V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V, f = 0	V _{CC} = LL	1	15		1	15	
			V _{CC} = Automotive				1	20	
			V _{CC} = SL	1	5		1	5	

Capacitance^[5]

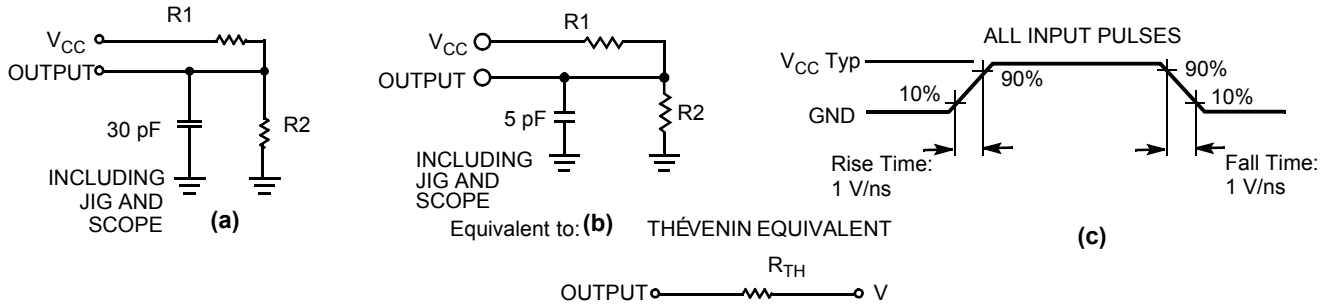
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = V _{CC(typ)}	6	pF
C _{OUT}	Output Capacitance		8	pF

Thermal Resistance

Description	Test Conditions	Symbol	TSOPII	Unit
Thermal Resistance (Junction to Ambient) ^[5]	Still Air, soldered on a 4.25 x 1.125 inch, 4-layer printed circuit board	Θ _{JA}	60	°C/W
Thermal Resistance (Junction to Case) ^[5]		Θ _{JC}	22	°C/W

Notes:

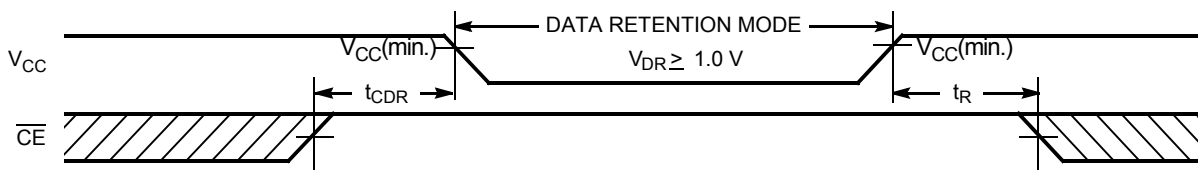
- 4. V_{IL(min.)} = -2.0V for pulse durations less than 20 ns.
- 5. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms


Parameters	3.0V	Unit
R1	1105	Ohms
R2	1550	Ohms
R _{TH}	645	Ohms
V _{TH}	1.75	Volts

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ. ^[3]	Max.	Unit
V _{DR}	V _{CC} for Data Retention		1.0			V
I _{CCDR}	Data Retention Current	V _{CC} = 1.0V, $\overline{CE} \geq V_{CC} - 0.3V$, V _{IN} ≥ V _{CC} - 0.3V or V _{IN} ≤ 0.3V; No input may exceed; V _{CC} +0.3V		0.5	7.5	μA
		LL				
		Automotive			10	
		SL		0.5	5	
t _{CDR} ^[5]	Chip Deselect to Data Retention Time		0			ns
t _R	Operation Recovery Time		70			ns

Data Retention Waveform


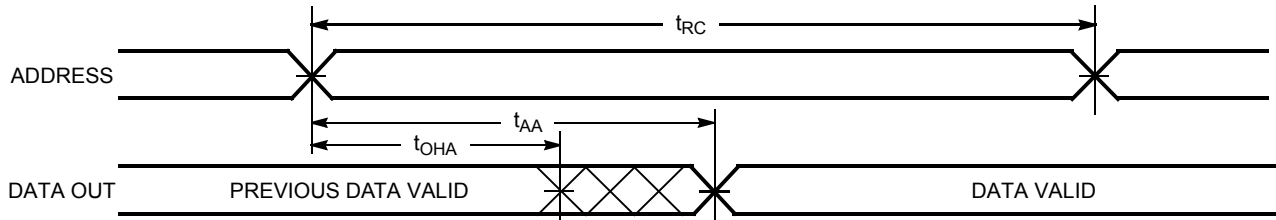
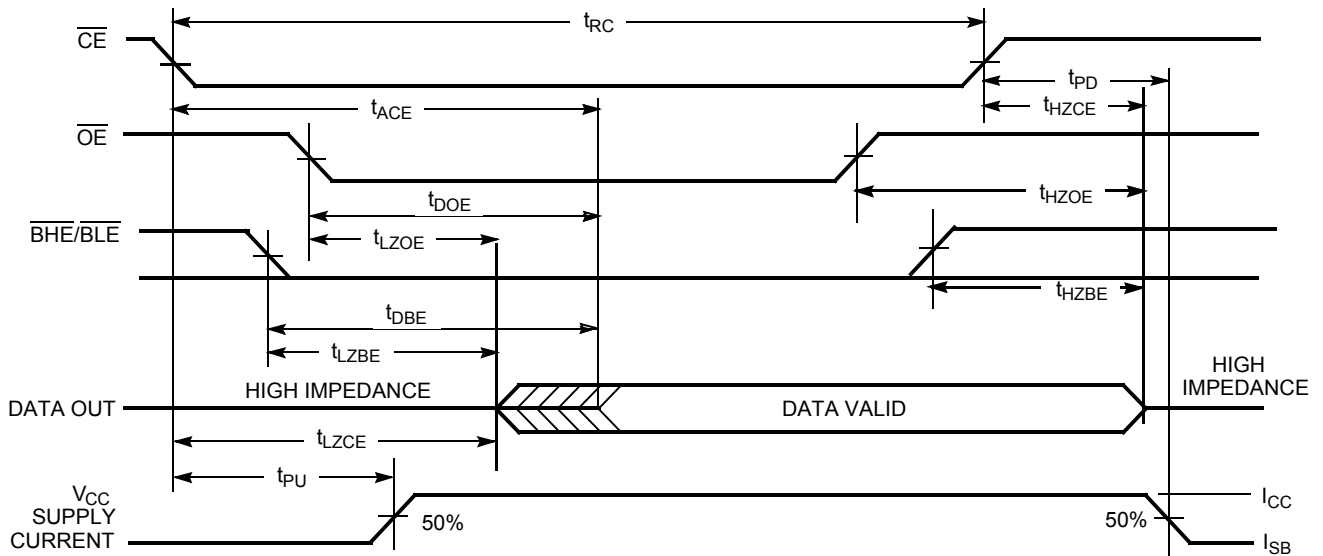


Switching Characteristics Over the Operating Range [6]

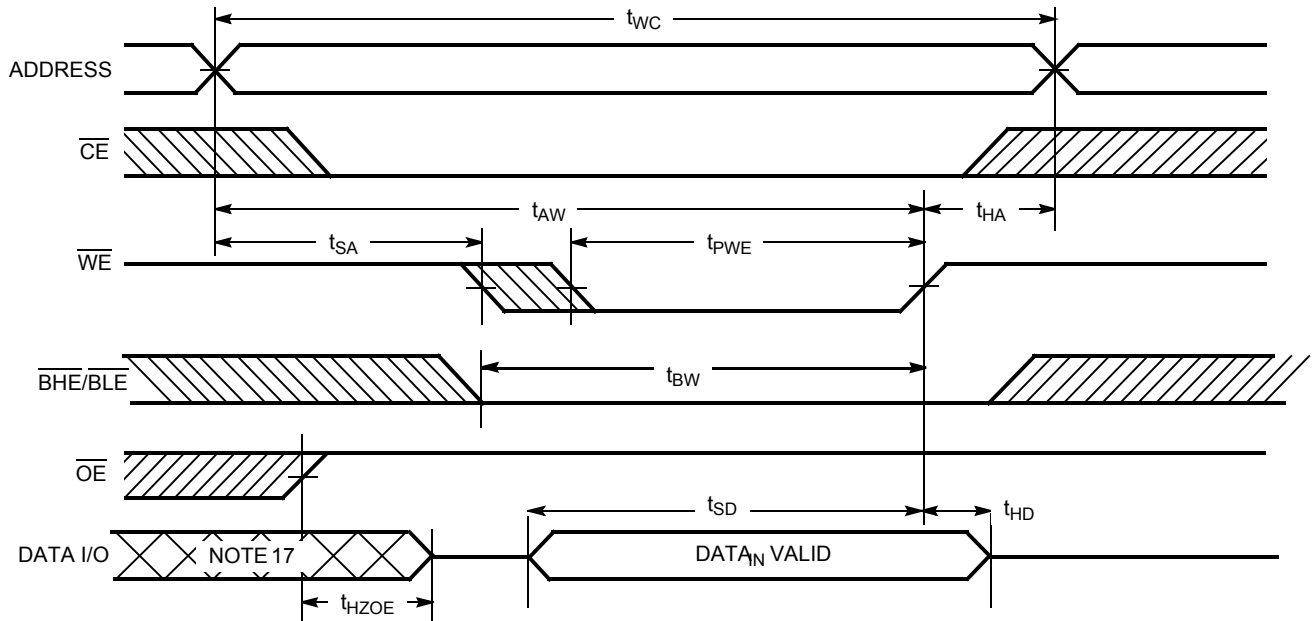
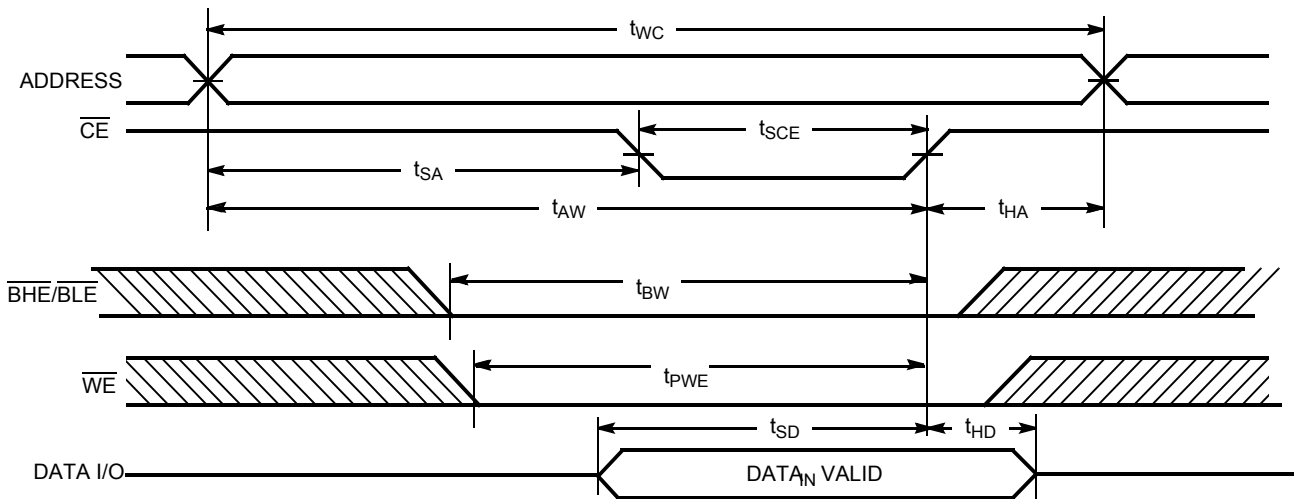
Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t _{RC}	Read Cycle Time	55		70		ns
t _{AA}	Address to Data Valid		55		70	ns
t _{OHA}	Data Hold from Address Change	10		10		ns
t _{ACE}	\overline{CE} LOW to Data Valid		55		70	ns
t _{DOE}	\overline{OE} LOW to Data Valid		25		35	ns
t _{LZOE}	\overline{OE} LOW to Low-Z ^[7]	5		5		ns
t _{HZOE}	\overline{OE} HIGH to High-Z ^[7, 8]		25		25	ns
t _{LZCE}	\overline{CE} LOW to Low-Z ^[7]	10		10		ns
t _{HZCE}	\overline{CE} HIGH to High-Z ^[7, 8]		25		25	ns
t _{PU}	\overline{CE} LOW to Power-up	0		0		ns
t _{PD}	\overline{CE} HIGH to Power-down		55		70	ns
t _{DBE}	\overline{BHE} / \overline{BLE} LOW to Data Valid		55		70	ns
t _{LZBE} ⁽⁹⁾	\overline{BHE} / \overline{BLE} LOW to Low-Z	5		5		ns
t _{HZBE}	\overline{BHE} / \overline{BLE} HIGH to High-Z		25		25	ns
Write Cycle ^[10, 11]						
t _{WC}	Write Cycle Time	55		70		ns
t _{SCE}	\overline{CE} LOW to Write End	45		60		ns
t _{AW}	Address Set-up to Write End	45		60		ns
t _{HA}	Address Hold from Write End	0		0		ns
t _{SA}	Address Set-up to Write Start	0		0		ns
t _{PWE}	\overline{WE} Pulse Width	40		50		ns
t _{SD}	Data Set-up to Write End	25		30		ns
t _{HD}	Data Hold from Write End	0		0		ns
t _{HZWE}	\overline{WE} LOW to High-Z ^[7, 8]		20		25	ns
t _{LZWE}	\overline{WE} HIGH to Low-Z ^[7]	5		10		ns
t _{BW}	\overline{BHE} / \overline{BLE} LOW to End of Write	50		60		ns

Notes:

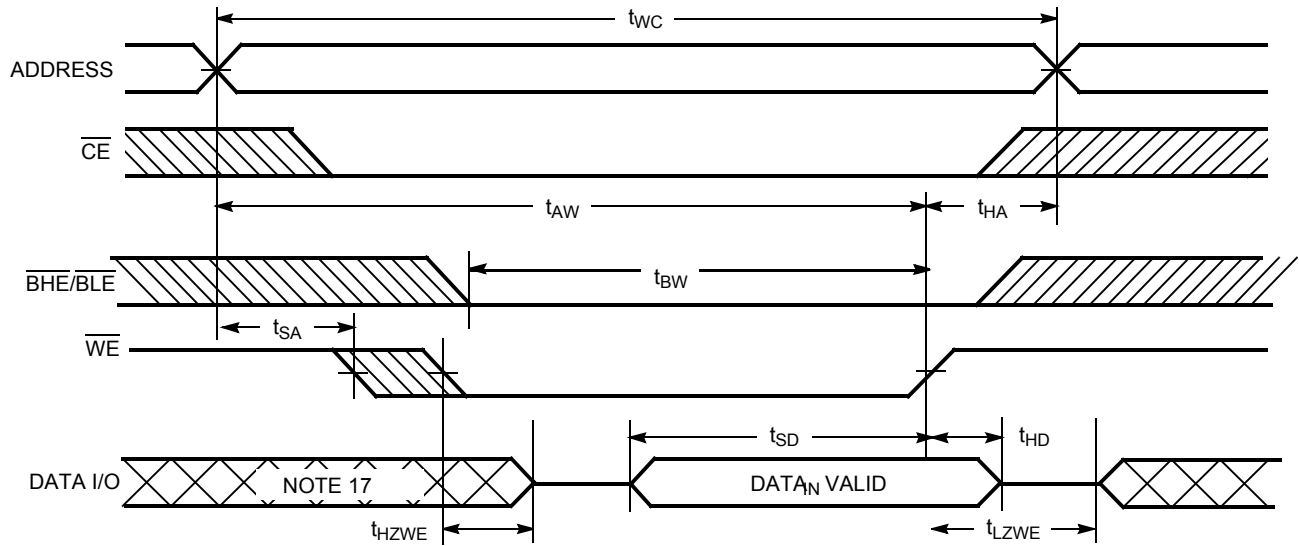
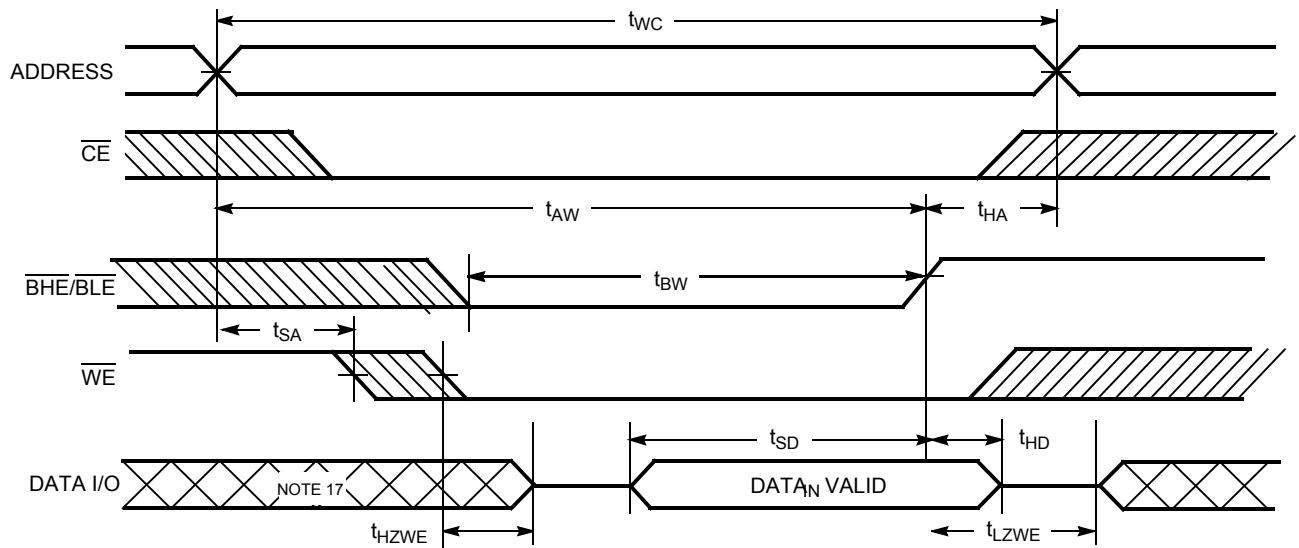
- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input levels of 0 to V_{CC} typ., and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
- t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
- If both byte enables are toggled together this value is 10 ns.
- The internal write time of the memory is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
- The minimum write cycle time for write cycle #3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD}.

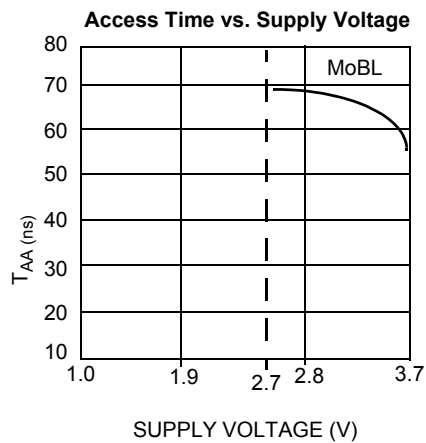
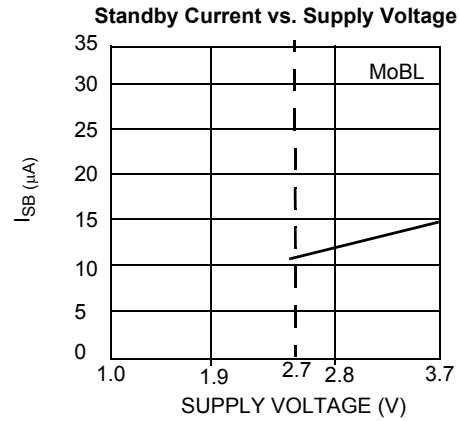
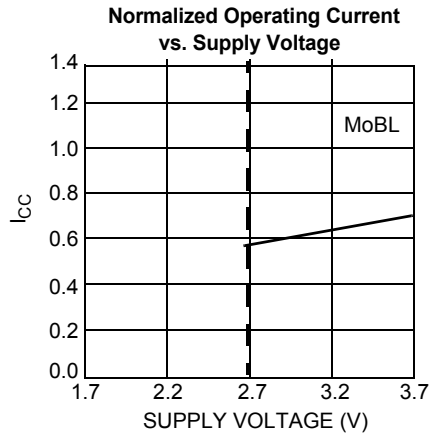
Switching Waveforms
Read Cycle No. 1 ^[12, 13]

Read Cycle No. 2 ^[13, 14]

Notes:

12. Device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
13. WE is HIGH for read cycle.
14. Address valid prior to or coincident with \overline{CE} transition LOW.

Switching Waveforms (continued)
Write Cycle No. 1 (\overline{WE} Controlled) ^[10, 15, 16]

Write Cycle No. 2 (\overline{CE} Controlled) ^[10, 15, 16]

Notes:

15. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
16. If \overline{CE} goes HIGH simultaneously with \overline{WE} HIGH, the output remains in a high-impedance state.
17. During this period, the I/Os are in output state and input signals should not be applied.

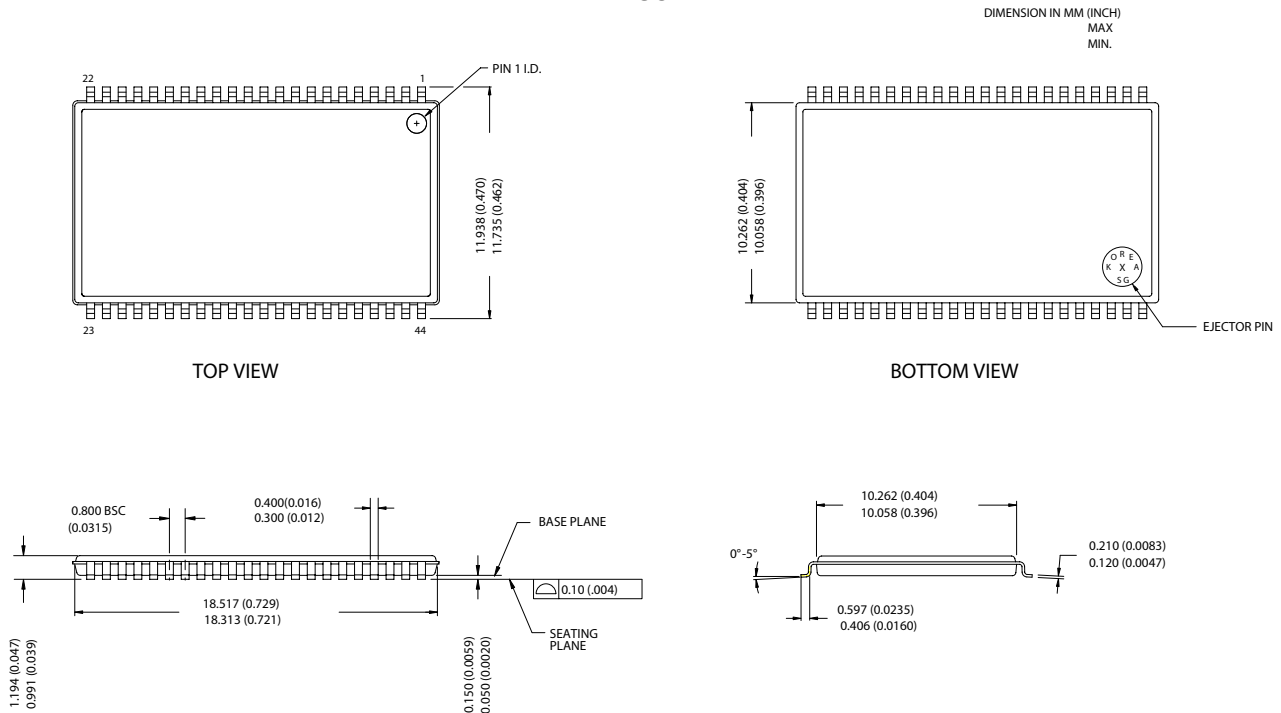
Switching Waveforms (continued)
Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW)^[11, 16]

Write Cycle No. 4 ($\overline{BHE}/\overline{BLE}$ Controlled, \overline{OE} LOW)^[17]


Typical DC and AC Characteristics

Truth Table

\overline{CE}	\overline{WE}	\overline{OE}	\overline{BHE}	\overline{BLE}	Inputs/Outputs	Mode	Power
H	X	X	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
L	X	X	H	H	High-Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_0 – I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_0 – I/O_7); I/O_8 – I/O_{15} in High-Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8 – I/O_{15}); I/O_0 – I/O_7 in High-Z	Read	Active (I_{CC})
L	H	H	L	L	High-Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	H	L	High-Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	L	H	High-Z	Deselect/Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0 – I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_0 – I/O_7); I/O_8 – I/O_{15} in High-Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8 – I/O_{15}); I/O_0 – I/O_7 in High-Z	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62137VLL-55ZI	Z44	44-pin TSOP II	Industrial
	CY62137VSL-55ZI			
70	CY62137VLL-70ZI			
	CY62137VSL-70ZI			
	CY62137VLL-70ZE	Automotive		

Package Diagrams
44-Pin TSOP II Z44


51-85087-*A

MoBL is a registered trademark, and More Battery Life is a trademark, of Cypress Semiconductor. All product and company names mentioned in this document are the trademarks of their respective holders.



Document Title: CY62137V MoBL[®] 2M (128K x 16) Static RAM				
Document Number: 38-05051				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	109960	10/03/01	SZV	Changed from Spec number: 38-00738 to 38-05051
*A	116788	09/04/02	GBI	Added footnote number one. Added SL power bin. Deleted fBGA package; replacement fBGA package is available in CY62137CV30.
*B	237428	See ECN	AJU	Added Automotive product information